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LMV821 Single/ LMV822 Dual/ LMV824 Quad Low Voltage, Low Power, R-to-R Output, 5 MHz Op Amps

General Description

The LMV821/LMV822/LMV824 bring performance and economy to low voltage / low power systems. With a 5 MHz unity-gain frequency and a guaranteed 1.4 V/us slew rate, the quiescent current is only 220 µA/amplifier (2.7 V). They provide rail-to-rail (R-to-R) output swing into heavy loads (600 Ω Guarantees). The input common-mode voltage range includes ground, and the maximum input offset voltage is 3.5mV (Guaranteed). They are also capable of comfortably driving large capacitive loads (refer to the application notes section).

The LMV821 (single) is available in the ultra tiny SC70-5 package, which is about half the size of the previous title holder, the SOT23-5.

Overall, the LMV821/LMV822/LMV824 (Single/Dual/Quad) are low voltage, low power, performance op amps, that can be designed into a wide range of applications, at an economical price.

Features

(For Typical, 5 V Supply Values; Unless Otherwise Noted) ■ Ultra Tiny, SC70-5 Package 2.0 x 2.0 x 1.0 mm

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 $\Delta \sim 10^4$

Absolute Maximum Ratings (Note 1)

 $\alpha=1$

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

ESD Tolerance (Note 2) Machine Model 100V Human Body Model LMV822/824 2000V LMV821 1500V Differential Input Voltage \pm Supply Voltage Supply Voltage (V⁺-V ⁻) 5.5V Output Short Circuit to V⁺ (Note 3) Output Short Circuit to V[−] (Note 3) Soldering Information

Operating Ratings (Note 1)

2.7V DC Electrical Characteristics

Infrared or Convection (20 sec) 235°C Storage Temperature Range -65° C to 150°C Junction Temperature (Note 4) 150°C

Unless otherwise specified, all limits guaranteed for T_J = 25°C. V⁺ = 2.7V, V [−] = 0V, V_{CM} = 1.0V, V_O = 1.35V and R_L > 1 MΩ.
Boldface limits apply at the temperature extremes.

2.5V DC Electrical Characteristics

Unless otherwise specified, all limits guaranteed for T_J = 25°C. V⁺ = 2.5V, V [−] = 0V, V_{CM} = 1.0V, V_O = 1.25V and R_L > 1 MΩ.
Boldface limits apply at the temperature extremes.

2.7V AC Electrical Characteristics

Unless otherwise specified, all limits guaranteed for T_J = 25°C. V⁺ = 2.7V, V [−] = 0V, V_{CM} = 1.0V, V_O = 1.35V and R_L > 1 MΩ.
Boldface limits apply at the temperature extremes.

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 $\omega_{\rm{eff}}=2\pi$

2.7V AC Electrical Characteristics (Continued)

Unless otherwise specified, all limits guaranteed for T_J = 25°C. V⁺ = 2.7V, V [−] = 0V, V_{CM} = 1.0V, V_O = 1.35V and R_L > 1 MΩ.
Boldface limits apply at the temperature extremes.

5V DC Electrical Characteristics

 \mathcal{L}^{max}

Unless otherwise specified, all limits guaranteed for T_J = 25°C. V⁺ = 5V, V ⁻ = 0V, V_{CM} = 2.0V, V_O = 2.5V and R _L > 1 MΩ.
Boldface limits apply at the temperature extremes.

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5V DC Electrical Characteristics (Continued)

 \mathcal{L}^{max}

Unless otherwise specified, all limits guaranteed for T_J = 25℃. V⁺ = 5V, V ⁻ = 0V, V_{CM} = 2.0V, V_O = 2.5V and R _L > 1 MΩ. **Boldface** limits apply at the temperature extremes.

5V AC Electrical Characteristics

Unless otherwise specified, all limits guaranteed for T_J = 25[°]C. V⁺ = 5V, V[−] = 0V, V_{CM} = 2V, V_O = 2.5V and R_L > 1 MΩ. **Boldface** limits apply at the temperature extremes.

Note 1: Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is intended to be functional, but specific performance is not guaranteed. For guaranteed specifications and the test conditions, see the Electrical Characteristics. **Note 2:** Human body model, 1.5 kΩ in series wth 100 pF. Machine model, 200Ω in series with 100 pF.

Note 3: Applies to both single-supply and split-supply operation. Continuous short circuit operation at elevated ambient temperature can result in exceeding the
maximum allowed junction temperature of 150°C. Output curre

Note 4: The maximum power dissipation is a function of T_{J(max)} , θ _{JA}, and T_A. The maximum allowable power dissipation at any ambient temperature is P_D = (T_J·
_(max)–T _A)/θ_{JA}. All numbers apply for pack

Note 5: Typical Values represent the most likely parametric norm.

Note 6: All limits are guaranteed by testing or statistical analysis.

Note 7: V⁺ = 5V. Connected as voltage follower with 3V step input. Number specified is the slower of the positive and negative slew rates.

Note 8: Input referred, $V^+ = 5V$ and $R_L = 100$ k Ω connected to 2.5V. Each amp excited in turn with 1 kHz to produce V $_0 = 3$ V_{PP}.

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APPLICATION NOTE

This application note is divided into two sections: design considerations and Application Circuits.

1.0 Design Considerations

- This section covers the following design considerations:
- 1. Frequency and Phase Response Considerations
- 2. Unity-Gain Pulse Response Considerations
- 3. Input Bias Current Considerations

1.1 Frequency and Phase Response Considerations

The relationship between open-loop frequency response and open-loop phase response determines the closed-loop stability performance (negative feedback). The open-loop phase response causes the feedback signal to shift towards becoming positive feedback, thus becoming unstable. The further the output phase angle is from the input phase angle, the more stable the negative feedback will operate. Phase Margin (ϕ_m) specifies this output-to-input phase relationship at the unity-gain crossover point. Zero degrees of phasemargin means that the input and output are completely in phase with each other and will sustain oscillation at the unitygain frequency.

The AC tables show ϕ_m for a no load condition. But ϕ_m changes with load. The Gain and Phase margin vs Frequency plots in the curve section can be used to graphically determine the ϕ_m for various loaded conditions. To do this, examine the phase angle portion of the plot, find the phase margin point at the unity-gain frequency, and determine how far this point is from zero degree of phase-margin. The larger the phase-margin, the more stable the circuit operation.

The bandwidth is also affected by load. The graphs of Figure ¹ and Figure ² provide a quick look at how various loads affect the ϕ_m and the bandwidth of the LMV821/822/824 family. These graphs show capacitive loads reducing both ϕ_m and bandwidth, while resistive loads reduce the bandwidth but increase the $φ_m$. Notice how a 600 $Ω$ resistor can be added in parallel with 220 picofarads capacitance, to increase the ϕ_m 20˚(approx.), but at the price of about a 100 kHz of bandwidth.

Overall, the LMV821/822/824 family provides good stability for loaded condition.

Voltage for Various Loads

1.2 Unity Gain Pulse Response Considerations

A pull-up resistor is well suited for increasing unity-gain, pulse response stability. For example, a 600 Ω pull-up resistor reduces the overshoot voltage by about 50%, when driving a 220 pF load. Figure ³ shows how to implement the pull-up resistor for more pulse response stability.

FIGURE 3. Using a Pull-up Resistor at the Output for Stabilizing Capacitive Loads

Higher capacitances can be driven by decreasing the value of the pull-up resistor, but its value shouldn't be reduced beyond the sinking capability of the part. An alternate approach is to use an isolation resistor as illustrated in Figure 4.

Figure ⁵ shows the resulting pulse response from a LMV824, while driving a 10,000pF load through a 20 Ω isolation resistor.

FIGURE 4. Using an Isolation Resistor to Drive Heavy Capacitive Loads

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FIGURE 5. Pulse Response per Figure ⁴

1.3 Input Bias Current Consideration

Input bias current (I_B) can develop a somewhat significant offset voltage. This offset is primarily due to I_B flowing through the negative feedback resistor, R_F . For example, if I_B is 90nA (max room) and R_F is 100 kΩ, then an offset of 9 mV will be developed (V_{OS} = I_Bx R_F). Using a compensation resistor (R_C) , as shown in Figure 6, cancels out this affect. But the input offset current (I_{OS}) will still contribute to an offset voltage in the same manner - typically 0.05 mV at room temp.

FIGURE 6. Canceling the Voltage Offset Effect of Input Bias Current

2.0 APPLICATION CIRCUITS

This section covers the following application circuits:

- 1. Telephone-Line Transceiver
- 2. "Simple" Mixer (Amplitude Modulator)
- 3. Dual Amplifier Active Filters (DAAFs)
- a. Low-Pass Filter (LPF)
- b. High-Pass Filter (HPF)
- 5. Tri-level Voltage Detector

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2.1 Telephone-Line Transceiver

The telephone-line transceiver of Figure 7 provides a fullduplexed connection through a PCMCIA, miniature transformer. The differential configuration of receiver portion (UR), cancels reception from the transmitter portion (UT). Note that the input signals for the differential configuration of UR, are the transmit voltage (Vt) and Vt/2. This is because R_{match} is chosen to match the coupled telephone-line impedance; therefore dividing Vt by two (assuming $R1 \gt R$ _{match}). The differential configuration of UR has its resistors chosen to cancel the Vt and Vt/2 inputs according to the following equation:

$$
V_0 = V_T \left(\frac{R_3}{R_3 + R_4}\right) \left(1 + \frac{R_2}{R_1}\right) - \frac{V_T}{2} \left(\frac{R_2}{R_1}\right) = V_T \frac{1}{3} (3) - \frac{V_T}{2} (2) = 0
$$

FIGURE 7. Telephone-line Transceiver for a PCMCIA Modem Card

Note that Cr is included for canceling out the inadequacies of the lossy, miniature transformer. Refer to application note AN-397 for detailed explanation.

2.2"Simple" Mixer (Amplitude Modulator)

The mixer of $Figure 8$ is simple and provides a unique form of amplitude modulation. Vi is the modulation frequency (F_M) , while a +3V square-wave at the gate of Q1, induces a carrier frequency (F_C) . Q1 switches (toggles) U1 between inverting and non-inverting unity gain configurations. Offsetting a sine wave above ground at Vi results in the oscilloscope photo of Figure 9.

The simple mixer can be applied to applications that utilize the Doppler Effect to measure the velocity of an object. The difference frequency is one of its output frequency components. This difference frequency magnitude (F_M-F_C) is the key factor for determining an object's velocity per the Doppler Effect. If a signal is transmitted to a moving object, the reflected frequency will be a different frequency. This difference in transmit and receive frequency is directly proportional to an object's velocity.

FIGURE 9. Output signal per the Circuit of Figure 8

2.4 Dual Amplifier Active Filters (DAAFs)

The LMV822/24 bring economy and performance to DAAFs. The low-pass and the high-pass filters of Figure 10 and Figure 11 (respectively), offer one key feature: excellent sensitivity performance. Good sensitivity is when deviations in component values cause relatively small deviations in a filter's parameter such as cutoff frequency (Fc). Single amplifier active filters like the Sallen-Key provide relatively poor sensitivity performance that sometimes cause problems for high production runs; their parameters are much more likely to deviate out of specification than a DAAF would. The DAAFs of Figure 10 and Figure ¹¹ are well suited for high volume production.

FIGURE 10. Dual Amplifier, 3 kHz Low-Pass Active Filter with a Butterworth Response and a Pass Band Gain of Times Two

FIGURE 11. Dual Amplifier, 300 Hz High-Pass Active Filter with a Butterworth Response and a Pass Band Gain of Times Two

Table 1 provides sensitivity measurements for a 10 MΩ load condition. The left column shows the passive components for the 3 kHz low-pass DAAF. The third column shows the components for the 300 Hz high-pass DAAF. Their respective sensitivity measurements are shown to the right of each component column. Their values consists of the percent change in cutoff frequency (Fc) divided by the percent change in component value. The lower the sensitivity value, the better the performance.

Each resistor value was changed by about 10 percent, and this measured change was divided into the measured change in Fc. A positive or negative sign in front of the measured value, represents the direction Fc changes relative to components' direction of change. For example, a sensitivity value of negative 1.2, means that for a 1 percent increase in component value, Fc decreases by 1.2 percent.

Note that this information provides insight on how to fine tune the cutoff frequency, if necessary. It should be also noted that R_4 and R_5 of each circuit also caused variations in the pass band gain. Increasing R_4 by ten percent, increased the gain by 0.4 dB, while increasing R_5 by ten percent, decreased the gain by 0.4 dB.

TABLE 1.

Active filters are also sensitive to an op amp's parameters -Gain and Bandwidth, in particular. The LMV822/24 provide a large gain and wide bandwidth. And DAAFs make excellent use of these feature specifications.

Single Amplifier versions require a large open-loop to closed-loop gain ratio - approximately 50 to 1, at the Fc of the filter response. Figure 12 shows an impressive photograph of a network analyzer measurement (hp3577A). The measurement was taken from a 300kHz version of Figure 10. At 300 kHz, the open-loop to closed-loop gain ratio $@$ Fc is about 5 to 1. This is 10 times lower than the 50 to 1 "rule of thumb" for Single Amplifier Active Filters.

FIGURE 12. 300 kHz, Low-Pass Filter, Butterworth Response as Measured by the HP3577A Network Analyzer

In addition to performance, DAAFs are relatively easy to design and implement. The design equations for the low-pass and high-pass DAAFs are shown below. The first two equation calculate the Fc and the circuit Quality Factor (Q) for the LPF (Figure 10). The second two equations calculate the Fc and Q for the HPF (Figure ¹¹).

(LPF)
$$
F_C = \frac{\sqrt{R_S}}{2\pi \sqrt{R_a} \cdot \sqrt{R_2} \cdot \sqrt{R_4} \cdot \sqrt{C_1} \cdot \sqrt{C_3}}
$$

$$
Q = 2\pi F_C \sqrt{C_1} \cdot \sqrt{C_3}
$$

$$
F_C = \frac{\sqrt{R_A}}{2\pi \sqrt{R_1} \cdot \sqrt{R_3} \cdot \sqrt{R_5} \cdot \sqrt{C_2} \cdot \sqrt{C_2}}
$$

$$
Q = 2\pi F_C \sqrt{C_a} \cdot \sqrt{C_2}
$$

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To simplify the design process, certain components are set equal to each other. Refer to Figure 10 and Figure ¹¹. These equal component values help to simplify the design equations as follows:

(LPF)
$$
R_a = R_2 = \frac{1}{2\pi F_C \sqrt{C_1} \cdot \sqrt{C_3}}
$$

\n $R_3 = \frac{Q}{2\pi F_C \sqrt{C_1} \cdot \sqrt{C_3}}$
\n(HPF) $R_1 = R_3 = \frac{1}{2\pi F_C \sqrt{C_a} \cdot \sqrt{C_2}}$
\n $R_b = \frac{Q}{2\pi F_C \sqrt{C_a} \cdot \sqrt{C_2}}$

To illustrate the design process/implementation, a 3 kHz, Butterworth response, low-pass filter DAAF (Figure 10) is designed as follows:

1. Choose $C_1 = C_3 = C = 1$ nF

2. Choose $R_4 = R_5 = 1$ kΩ

3. Calculate R_a and R_2 for the desired Fc as follows:

$$
R_{a} = R_{2} = \frac{1}{2\pi(F_{C})C}
$$

=
$$
\frac{1}{2\pi(3 \text{ kHz})1nF}
$$

= 53.1 kΩ
= 53.6 kΩ (Practical Value)

4. Calculate R_3 for the desired Q. The desired Q for a Butterworth (Maximally Flat) response is 0.707 (45 degrees into the s-plane). R_3 calculates as follows:

$$
R_3 = \frac{Q}{2\pi (F_C)C}
$$

=
$$
\frac{0.707}{2\pi (3 \text{ kHz}) 1\text{ nF}}
$$

= 37.5 kΩ
\$37.4 kΩ (Practical Value)

Notice that R_3 could also be calculated as 0.707 of R_3 or R_2 . The circuit was implemented and its cutoff frequency measured. The cutoff frequency measured at 2.92 kHz.

The circuit also showed good repeatability. Ten different LMV822 samples were placed in the circuit. The corresponding change in the cutoff frequency was less than a percent.

2.5 Tri-level Voltage Detector

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The tri-level voltage detector of Figure 13 provides a type of window comparator function. It detects three different input voltage ranges: Min-range, Mid-range, and Max-range. The output voltage (\vee_{O}) is at \vee_{CC} for the Min-range. \vee_{O} is clamped at GND for the Mid-range. For the Max-range, $\mathtt{V}_\mathtt{O}$ is at V_{ee} . Figure 14 shows a V_{O} vs. V_{I} oscilloscope photo per the circuit of Figure 13.

Its operation is as follows: V_1 deviating from GND, causes the diode bridge to absorb I_{IN} to maintain a clamped condition (V_O= 0V). Eventually, I_{IN} reaches the bias limit of the di-
ode bridge. When this limit is reached, the clamping effect

FIGURE 13. Tri-level Voltage Detector

stops and the op amp responds open loop. The design equation directly preceding Figure ¹⁴, shows how to determine the clamping range. The equation solves for the input voltage band on each side GND. The mid-range is twice this voltage band.

$$
\Delta V = \frac{R}{R_1} (V_{CC} - V_{Diode})
$$
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SOT-23-5 Tape and Reel Specification

Tape Format

 $\omega_{\rm{max}}$

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 $\epsilon=1$

 \mathcal{L}^{\pm}

 $\hat{\mathcal{A}}$

 $\hat{\mathcal{E}}$

 $\hat{\boldsymbol{\theta}}$

 $\hat{\mathbf{r}}$

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